

Product Summary

BV _{DSS}	R _{D(S)} Max	I _D Max T _A = +25°C
30V	60mΩ @ V _{GS} = 10V	2.6A
	100mΩ @ V _{GS} = 4.5V	2.1A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

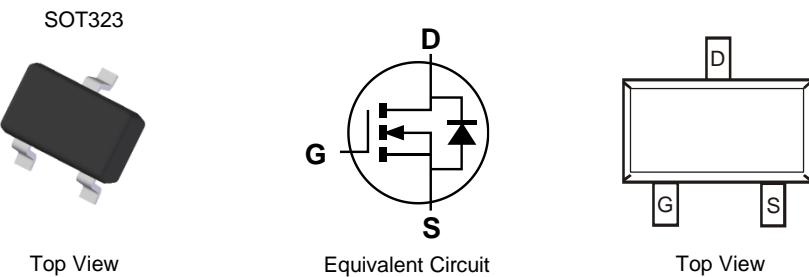
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- The DMN3060LWQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.027 grams (Approximate)



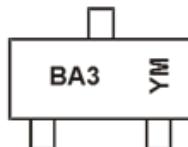
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3060LWQ-7	SOT323	3,000/Tape & Reel
DMN3060LWQ-13	SOT323	10,000/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



BA3 = Product Type Marking Code
 YM or YM = Date Code Marking
 Y or Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	H	I	J	K	L	M	N	O	P	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	2.6	A
				2.1	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	18	A
Maximum Body Diode Forward Current (Note 5)			I_S	0.68	A

 Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	251	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)		P_D	0.64	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	195	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

 Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current @ $T_C = +25^\circ\text{C}$	I_{DSS}	—	—	1.0	μA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.7	—	1.8	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	48	60	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 3.1\text{A}$
		—	51	100		$V_{GS} = 4.5\text{V}, I_D = 2\text{A}$
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	395	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.2\text{MHz}$
Output Capacitance	C_{oss}	—	39	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	26	—	pF	
Gate Resistance	R_g	—	3.1	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge	Q_g	—	5.6	—	nC	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V}, I_D = 6\text{A}$
Gate-Source Charge	Q_{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.8	—	ns	$V_{DD} = 10\text{V}, V_{GS} = 15\text{V}, R_L = 4.7\Omega, R_G = 3\Omega$
Turn-On Rise Time	t_R	—	30.8	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	18.3	—	ns	
Turn-Off Fall Time	t_F	—	2.7	—	ns	

Notes:

5. Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

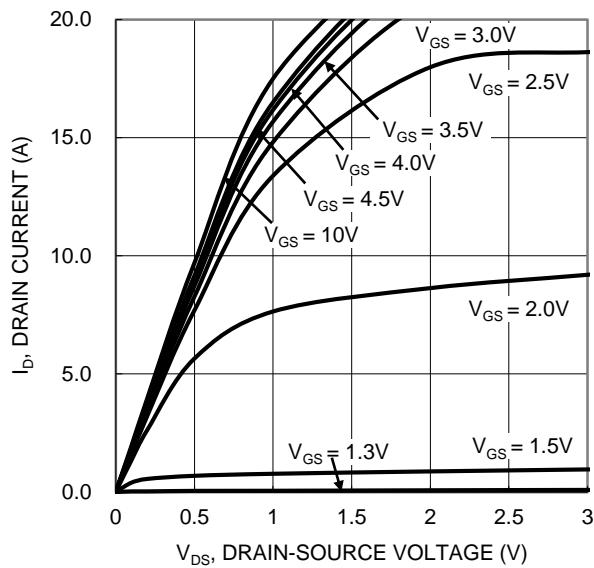


Figure 1. Typical Output Characteristic

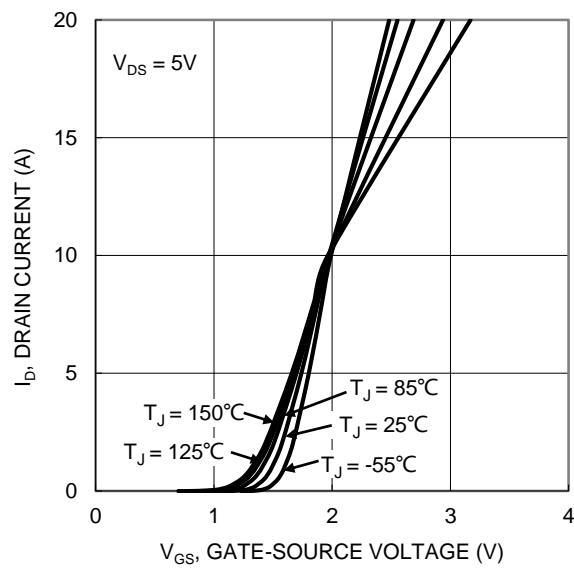


Figure 2. Typical Transfer Characteristic

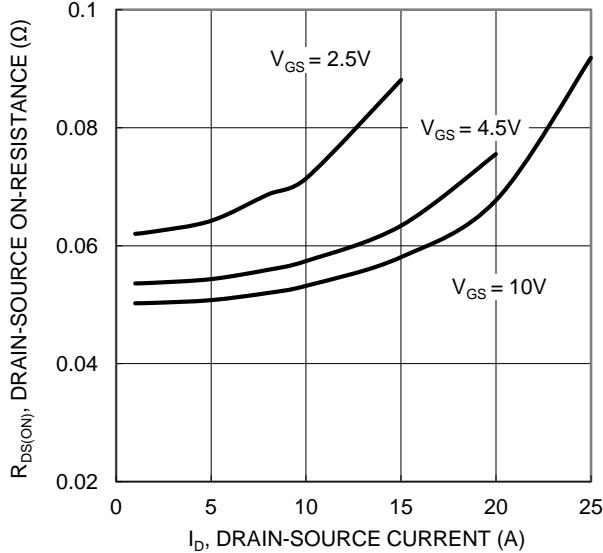


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

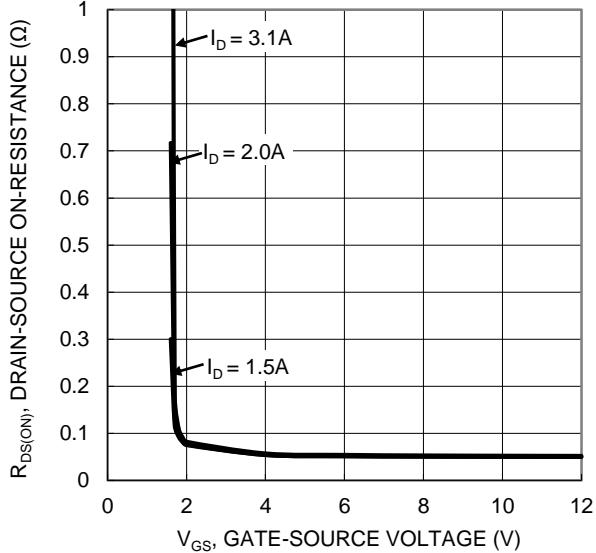


Figure 4. Typical Transfer Characteristic

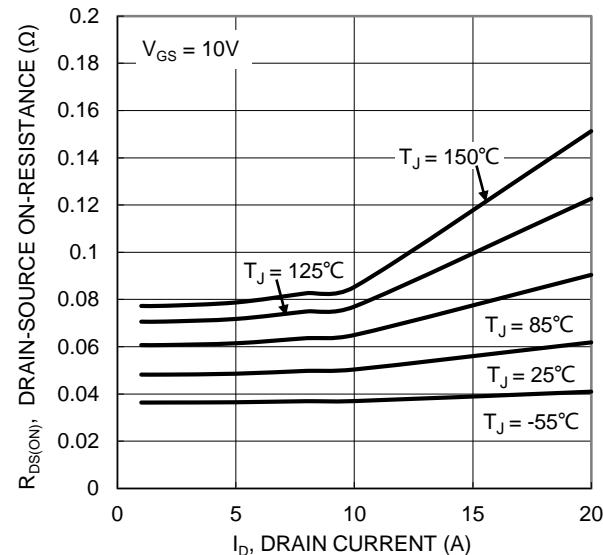


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

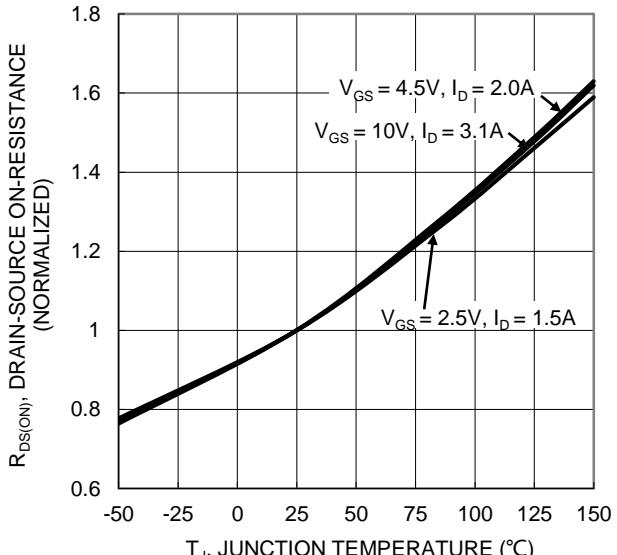


Figure 6. On-Resistance Variation with Junction Temperature

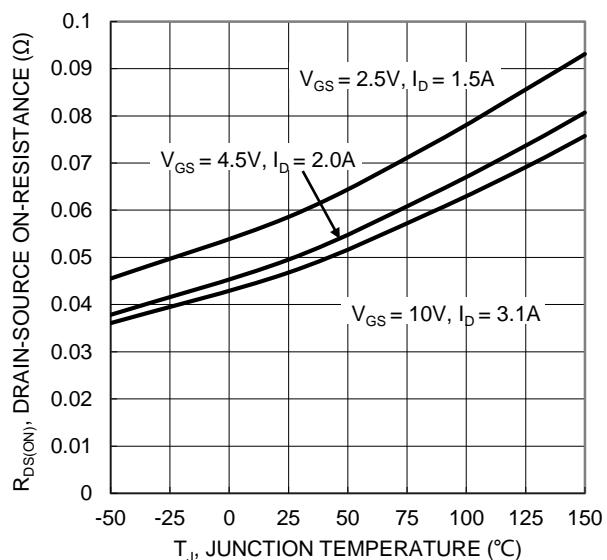


Figure 7. On-Resistance Variation with Junction Temperature

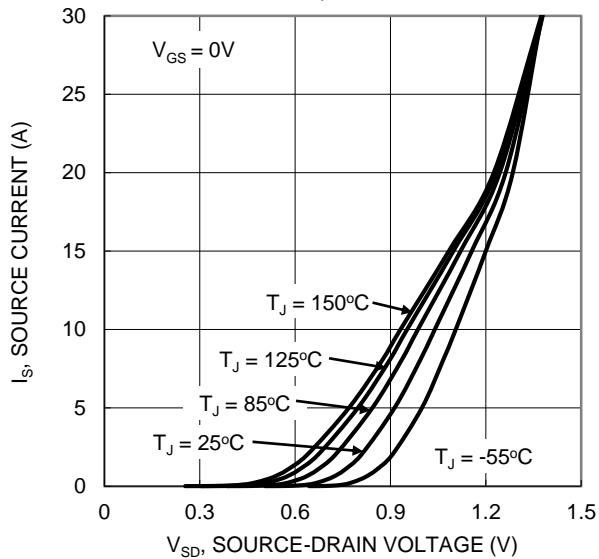


Figure 9. Diode Forward Voltage vs. Current

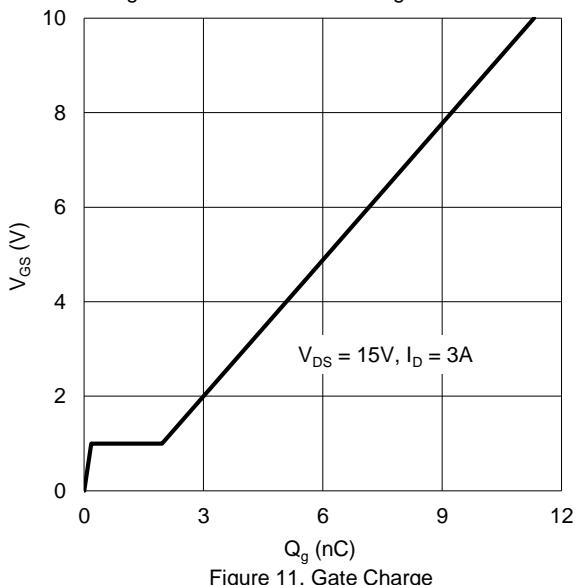


Figure 11. Gate Charge

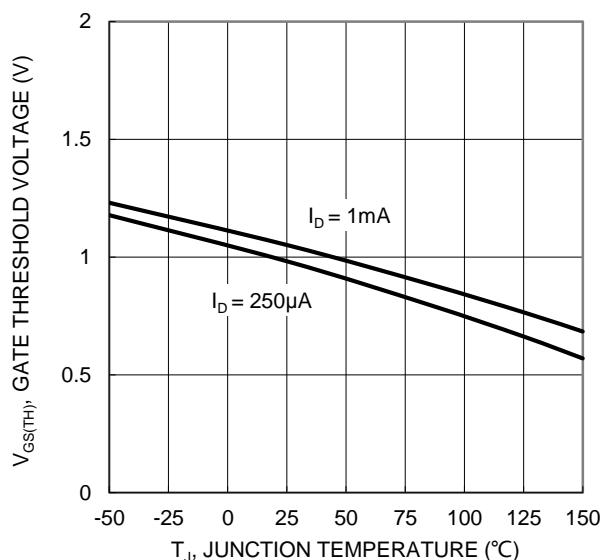


Figure 8. Gate Threshold Variation vs. Junction Temperature

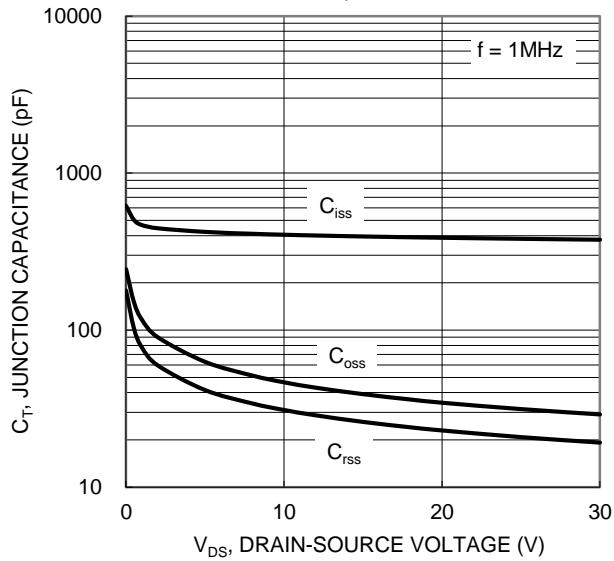


Figure 10. Typical Junction Capacitance

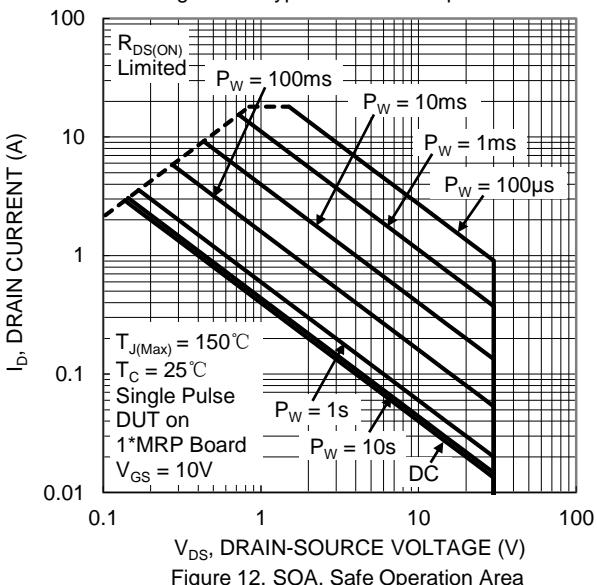


Figure 12. SOA, Safe Operation Area

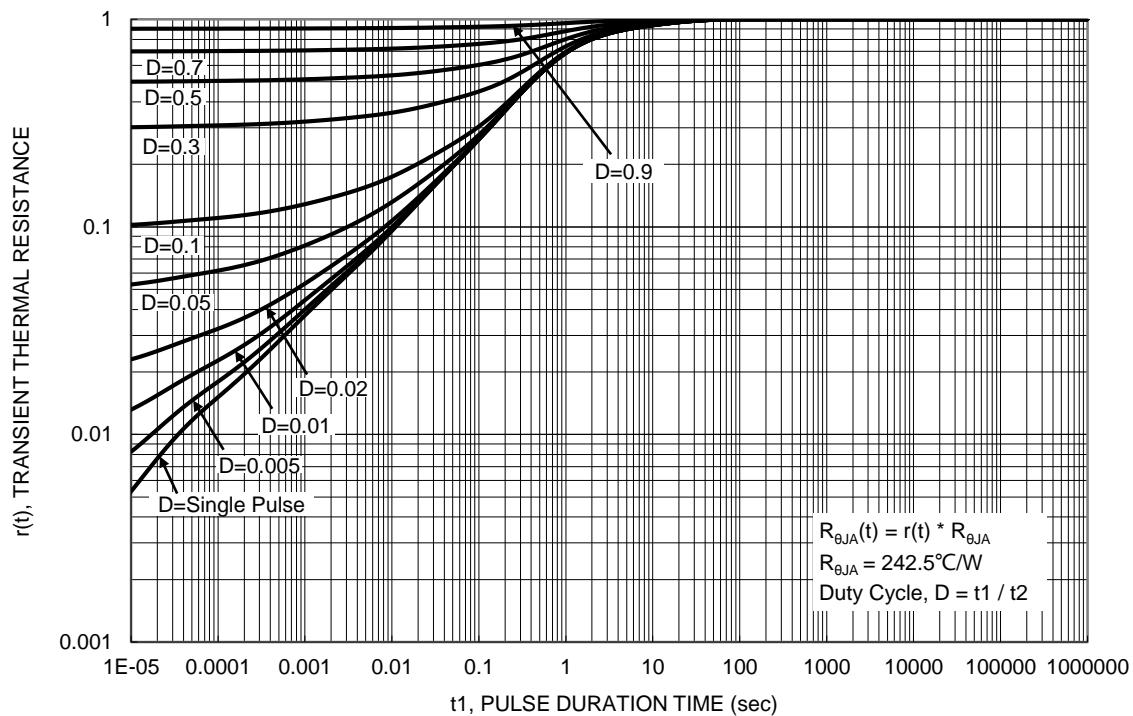
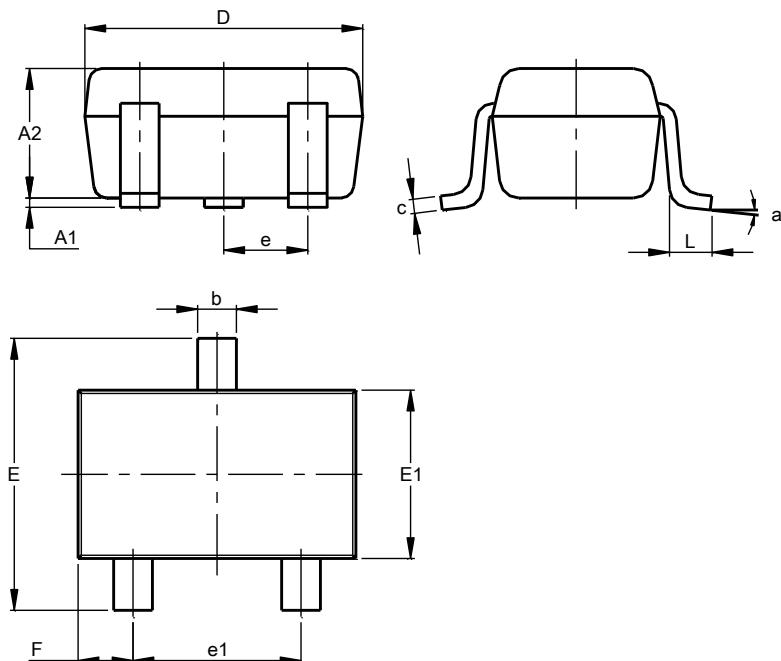


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323

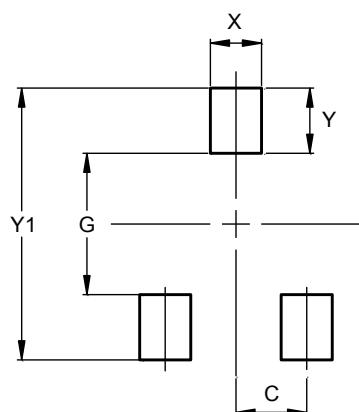


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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